HVM121WK

Silicon Epitaxial Planar PIN Diode for High Frequency Attenuator

HITACHI

ADE-208-042C (Z)
Preliminary, Rev. 3
Jun. 1993

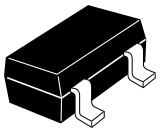
Features

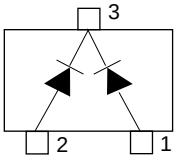
- Low capacitance. (C = 0.7pFmax)
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HVM121WK	H4	MPAK

Pin Arrangement





(Top View)

1 Anode
2 Anode
3 Cathode

Absolute Maximum Ratings (Ta = 25°C)

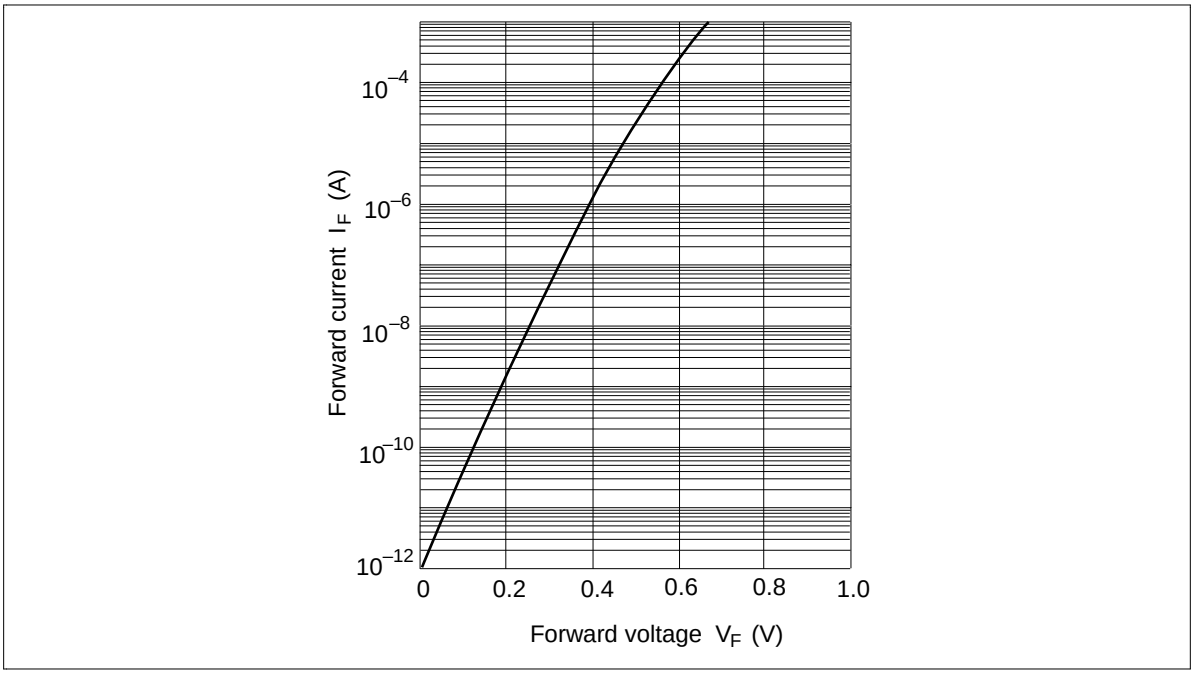
Item	Symbol	Value	Unit
Reverse voltage	V_R	100	V
Forward current	I_F	50	mA
Power dissipation	Pd*	100	mW
Junction temperature	Tj	125	°C
Storage temperature	Tstg	–55 to +125	°C

Note: Per one device

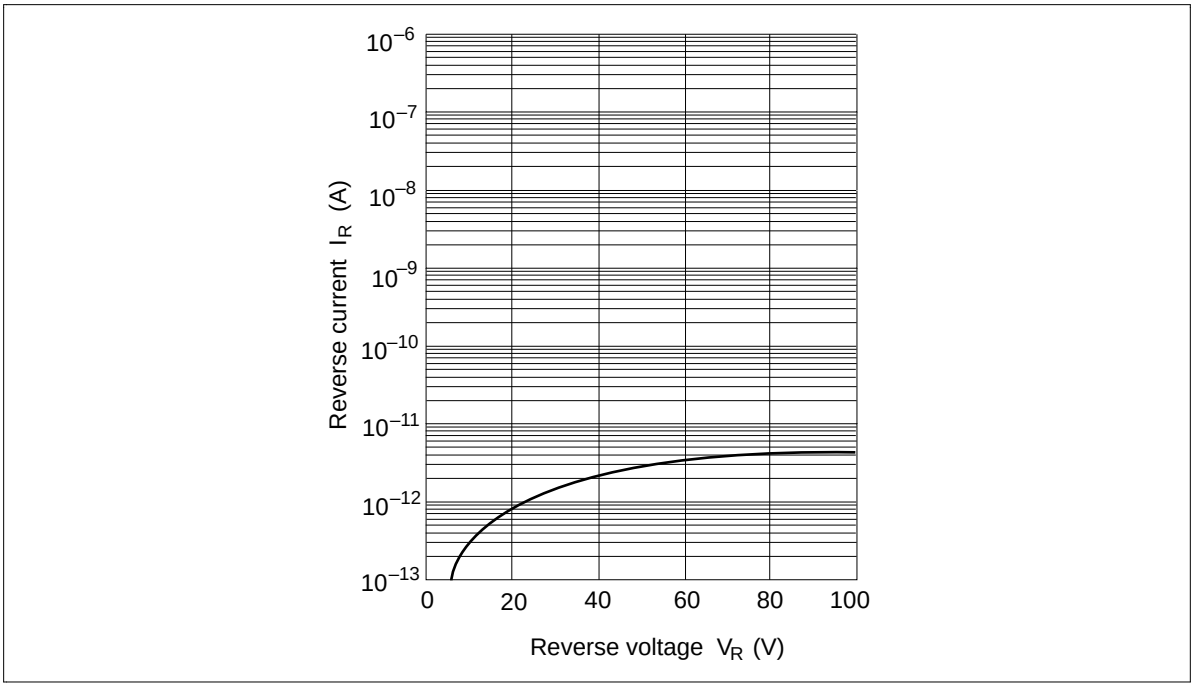
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.1	V	I_F = 50mA
Reverse current	I_R	—	—	100	nA	V_R = 30V
Capacitance	C	—	—	0.7	pF	V_R = 50V, f = 1MHz
Forward resistance	r_{f1}	1.0	—	—	kΩ	I_F = 10μA, f = 100MHz
	r_{f2}	—	—	10	Ω	I_F = 10mA, f = 100MHz

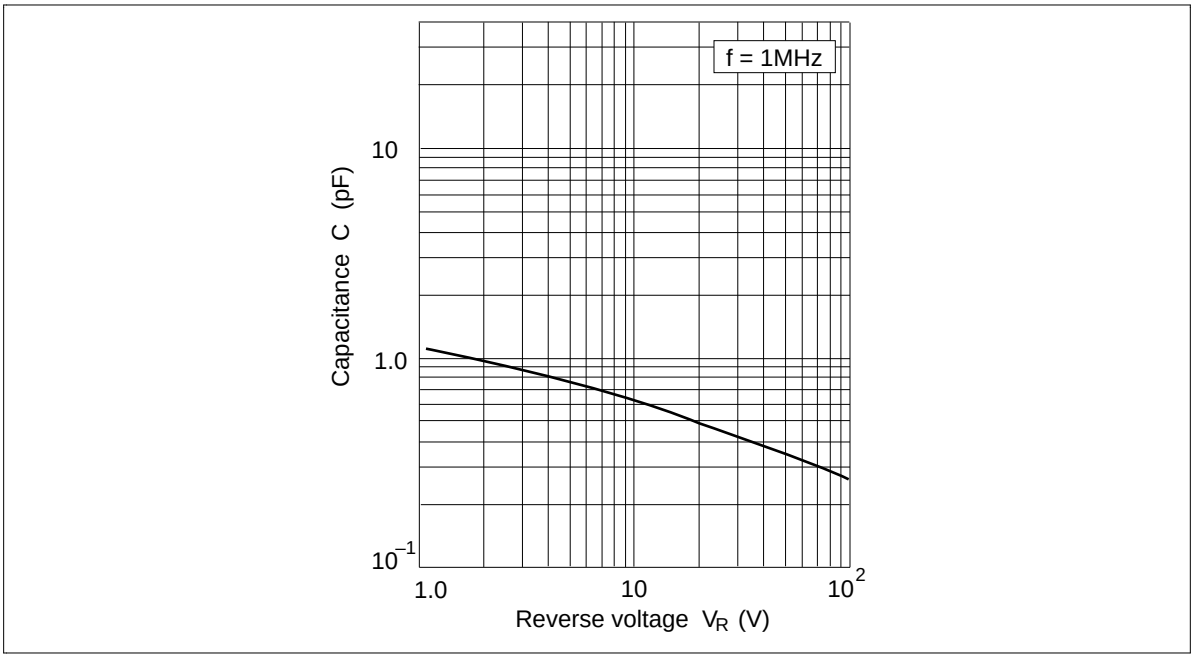
Forward current Vs. Forward voltage



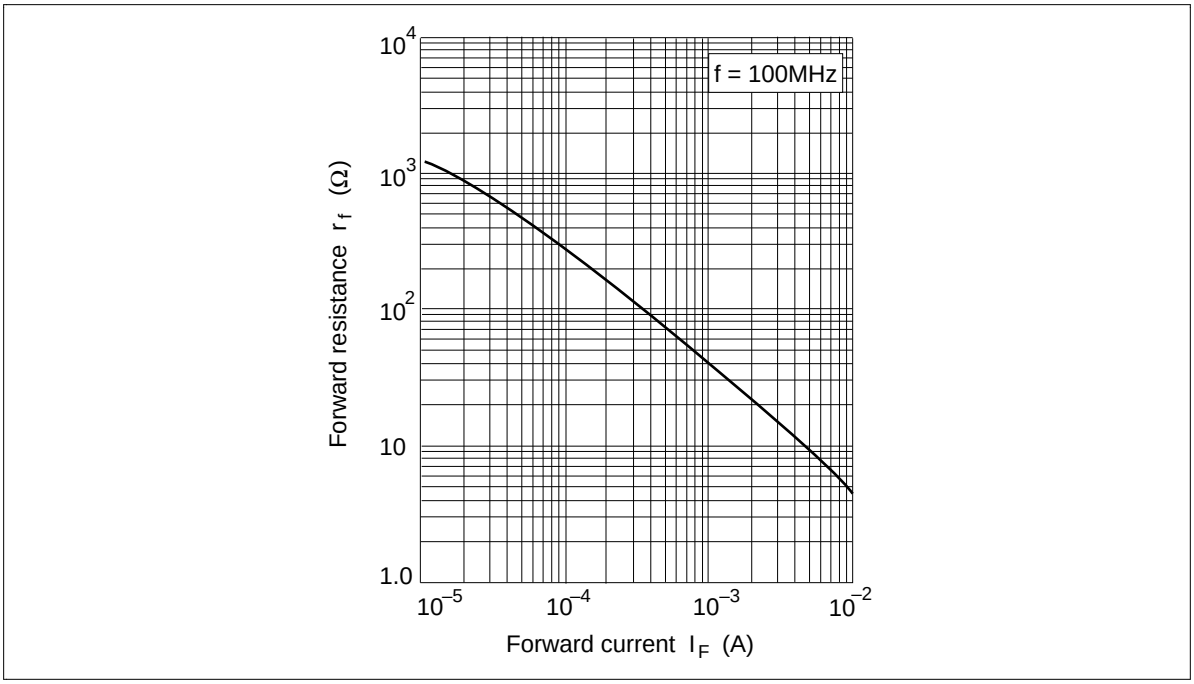
Reverse current Vs. Reverse voltage



Capacitance Vs. Reverse voltage

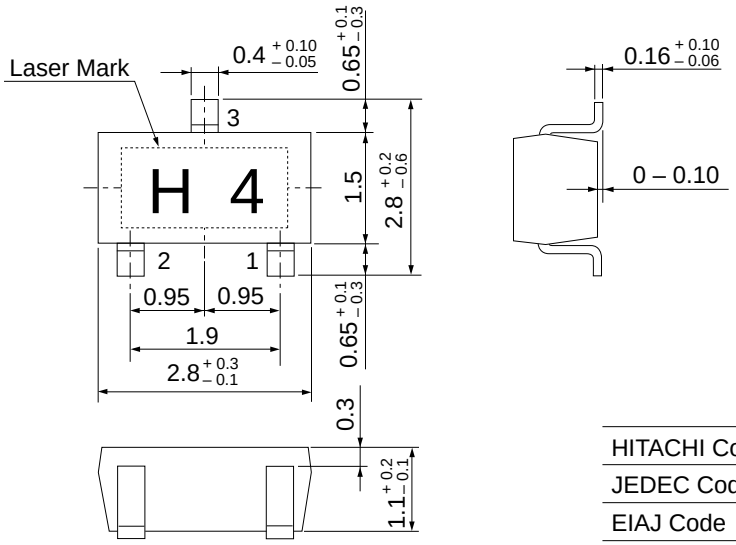


Forward resistance Vs. Forward current



Package Dimensions

Unit: mm



1 Anode
2 Anode
3 Cathode

HITACHI Code	MPAK(1)
JEDEC Code	—
EIAJ Code	SC-59A
Weight (g)	0.011